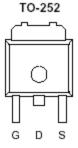
## P-Channel 100-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe DPAK saves board space
- Fast switching speed
- High performance trench technology

| PRODUCT SUMMARY            |                                 |    |  |  |
|----------------------------|---------------------------------|----|--|--|
| <b>V</b> <sub>DS</sub> (V) | $r_{DS(on)} m(\Omega) = I_D(A)$ |    |  |  |
| -100                       | $295 @V_{CS} = -10V$            | 11 |  |  |
|                            | $590 @V_{C8} = -4.5V$           | 8  |  |  |





Top View

| ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C UNLESS OTHERWISE NOTED) |                   |                 |            |       |  |
|--|-------------------|-----------------|------------|-------|--|
| Parameter  |                   |                 | Maximum    | Units |  |
| Drain-Source Voltage   |                   | V <sub>DS</sub> | -100       | V     |  |
| Cate-Source Voltage  |                   |                 | ±20        | v     |  |
| Continuous Drain Current <sup>a</sup>                            | $T_A=25^{\circ}C$ | I <sub>D</sub>  | 11         | А     |  |
| Pulsed Drain Current <sup>b</sup>                                |                   | I <sub>DM</sub> | ±40        | A     |  |
| Continuous Source Current (Diode Conduction) <sup>a</sup>        | Is                | -15             | Α          |       |  |
| Power Dissipation <sup>a</sup>                                   | $T_A=25^{\circ}C$ | PD              | 50         | W     |  |
| Operating Junction and Storage Temperature Range                 |                   | TJ, Tstg        | -55 to 175 | °C    |  |

| THERMAL RESISTANCE RATINGS               |                 |         |       |  |  |
|--|-----------------|---------|-------|--|--|
| Parameter                                | Symbol          | Maximum | Units |  |  |
| Maximum Junction-to-Ambient <sup>a</sup> | $R_{\theta JA}$ | 50      | °C/W  |  |  |
| Maximum Junction-to-Case                 | $R_{\theta JC}$ | 3.0     | °C/W  |  |  |

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

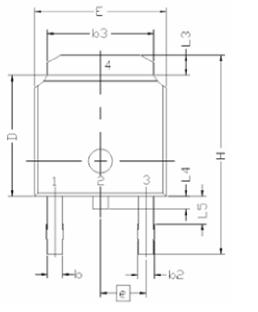
| SPECIFICATIONS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED) |                 |   |        |      |      |      |  |
|--|-----------------|---|--------|------|------|------|--|
| Derestor   | Gradial         |   | Limits |      |      | TL.4 |  |
| Parameter  | Symbol          | Test Conditions   | Min    | Тур  | Max  | Unit |  |
| Static   |                 |   |        |      |      |      |  |
| Gate-Threshold Voltage                                       | VGS(th)         | $V_{DS} = V_{GS}, I_D = -250  \text{uA}$  | -1     |      |      |      |  |
| Gate-Body Leakage  | IGSS            | $V_{DS} = 0 V, V_{GS} = \pm 20 V$   |        |      | ±100 | nA   |  |
| Zero Gate Voltage Drain Current                              | IDSS            | $V_{DS} = -80 V, V_{GS} = 0 V$  | )V     |      | -1   |      |  |
| Zero Gale voltage Dain Current                               | IDSS            | $V_{DS}$ = -80 V, $V_{GS}$ = 0 V, $T_J$ = 55°C  |        |      | -10  | uA   |  |
| On-State Drain Current <sup>A</sup>                          | ID(on)          | $V_{DS} = -5 V, V_{GS} = -10 V$   | -20    |      |      | Α    |  |
| A  |                 | $V_{GS}$ = -10 V, I <sub>D</sub> = -1 A   |        |      | 295  |      |  |
| Drain-Source On-Resistance <sup>A</sup>                      | fDS(on)         | $V_{GS}$ =-4.5 V, $I_D$ =-1 A   |        |      | 590  | mΩ   |  |
| Forward Tranconductance <sup>A</sup>                         | g <sub>íŝ</sub> | $V_{DS}$ =-15 V, $I_D$ =-28 A   |        | 8    |      | S    |  |
| Diode Forward Voltage  | Vsd             | $I_{\rm S}$ =-2.5 A, $V_{\rm GS}$ =0 V  |        | -0.7 |      | V    |  |
| Dynamic <sup>b</sup>   |                 |   |        |      |      |      |  |
| Total Gate Charge  | Qg              | $N_{} = 20 N N_{} = 45 N$   |        | 18   |      |      |  |
| Gate-Source Charge   | Qgs             | $V_{DS} = -30 \text{ V}, V_{GS} = -4.5 \text{ V},$<br>$I_D = -28 \text{ A}$   |        | 5    |      | nC   |  |
| Gate-Drain Charge  | Qgd             | ID=-28A   |        | 2    |      |      |  |
| Tum-On Delay Time  | td(on)          |   |        | 8    |      |      |  |
| Rise Time  | tr              | $V_{DD} = -30 \text{ V}, \text{ R}_{L} = 30 \Omega \text{ , ID} = -1 \text{ A},$ $V_{CEN} = -10 \text{ V}, \text{ R}_{G} = 6\Omega$ |        | 10   |      | nS   |  |
| Tum-Off Delay Time   | td(off)         |   |        | 35   |      |      |  |
| Fall-Time  | tf              |   |        | 12   |      |      |  |

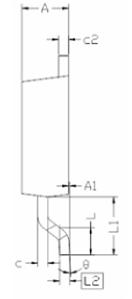
Notes

- a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

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## Package Information





|        | DIMENS |        | REQMIS |
|--------|--------|--------|--------|
| SYMBOL | MIN    | NDM    | MAX    |
| E      | 6.40   | 6.60   | 6.731  |
| L      | 1.40   | 1.52   | 1.77   |
| L1     | 2      | .743 R | ĒF     |
| L2     | 0.     | 508 BS | C      |
| L3     | 0.89   |        | 1.27   |
| L4     | 0.64   |        | 1.01   |
| L5     |        |        |        |
| D      | 6.00   | 6.10   | 6.223  |
| Н      | 9.40   | 10.00  | 10.40  |
| b      | 0.64   | 0.76   | 0.88   |
| b2     | 0.77   | 0.84   | 1.14   |
| b3     | 5.21   | 5.34   | 5.46   |
| e<br>A |        | 286 BS |        |
| A      | 2.20   | 2.30   | 2.38   |
| A1     | 0      |        | 0.127  |
| C      | 0.45   | 0.50   | 0.60   |
| c5     | 0.45   | 0.50   | 0.58   |
| D1     | 5.30   |        |        |
| E1     | 4.40   |        |        |
| Ū.     | 0*     |        | 10°    |

